

Product Summary

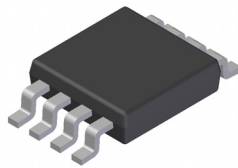
MOSFET		
$V_{(BR)DSS}$	$R_{DS(on) \max}$	I_D
-20V	85m Ω @ $V_{GS} = -10V$	-3.3A
	125m Ω @ $V_{GS} = -4.5V$	-2.8A
SCHOTTKY DIODE		
V_R	$V_F \max$	I_O
20V	400mV @ $I_F = 0.5A$	1.0A
	470mV @ $I_F = 1.0A$	

Description

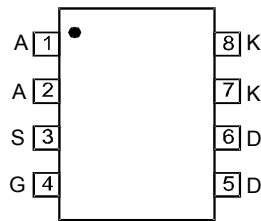
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting



Top View



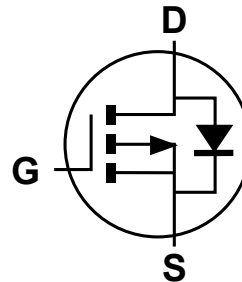
Top View
Internal Schematic

Features and Benefits

- Low Input Capacitance
- MOSFET with Low $R_{DS(ON)}$ – Minimize Conduction Losses
- Schottky Diode with Low Forward Voltage Drop
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.074 grams (approximate)



Q1 P-Channel MOSFET



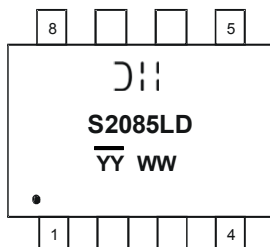
D1 Schottky Diode

Ordering Information (Note 4)

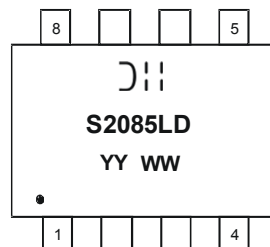
Part Number	Case	Packaging
DMS2085LSD-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

)|| = Manufacturer's Marking
 S2085LD = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 13 = 2013)
 WW = Week (01 - 53)
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings – P-CHANNEL MOSFET – Q1 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-3.3 -2.7	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-4.3 -3.4	A
Maximum Body Diode Forward Current (Note 6)			I_S	-1.5	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	-11.2	A
Avalanche Current (Notes 7) $L = 5\text{mH}$			I_{AR}	-5	A
Avalanche Energy (Notes 7) $L = 5\text{mH}$			E_{AR}	50	mJ

Maximum Ratings – SCHOTTKY – D1 (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	20	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Output Current (Note 7, $t < 10\text{s}$)	I_O	1	A
Peak Repetitive Forward Current (Note 7, $t < 10\text{s}$)	I_{FRM}	2	A
Non-Repetitive Peak Forward Surge Current (Note 7, $t < 10\text{s}$) Single half sine-wave superimposed on rated load	I_{FSM}	20	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	$T_A = +25^\circ\text{C}$	1.1
		$T_A = +70^\circ\text{C}$	1.8
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	Steady state	108
		$t < 10\text{s}$	65
Total Power Dissipation (Note 6)	P_D	$T_A = +25^\circ\text{C}$	1.8
		$T_A = +70^\circ\text{C}$	2.3
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	Steady state	78
		$t < 10\text{s}$	50
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	22	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	

Electrical Characteristics P-Channel Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	-1.5	-2.2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	70	85	mΩ	V _{GS} = -10V, I _D = -3.05A
		—	100	125		V _{GS} = -4.5V, I _D = -1.50A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.0	V	V _{GS} = 0V, I _S = -1.0A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	353	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	49	—		
Reverse Transfer Capacitance	C _{rss}	—	41	—		
Gate Resistance	R _G	—	6.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	3.7	—	nC	V _{DS} = -15V, I _D = -3A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	7.8	—		
Gate-Source Charge	Q _{gs}	—	1.1	—		
Gate-Drain Charge	Q _{gd}	—	1.3	—		
Turn-On Delay Time	t _{D(on)}	—	3.3	—	nS	V _{DS} = -15V, R _L = 15Ω V _{GS} = -10V, R _G = 6Ω
Turn-On Rise Time	t _r	—	3.0	—		
Turn-Off Delay Time	t _{D(off)}	—	14	—		
Turn-Off Fall Time	t _f	—	6.8	—		
Body Diode Reverse Recovery Time	t _{rr}	—	33	—	nS	I _S = -3.05A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	46	—	nC	I _S = -3.05A, dI/dt = 100A/μs

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

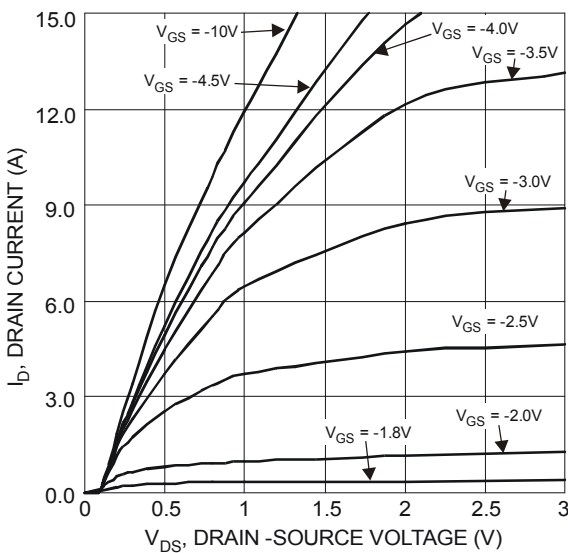


Figure 1 Typical Output Characteristics

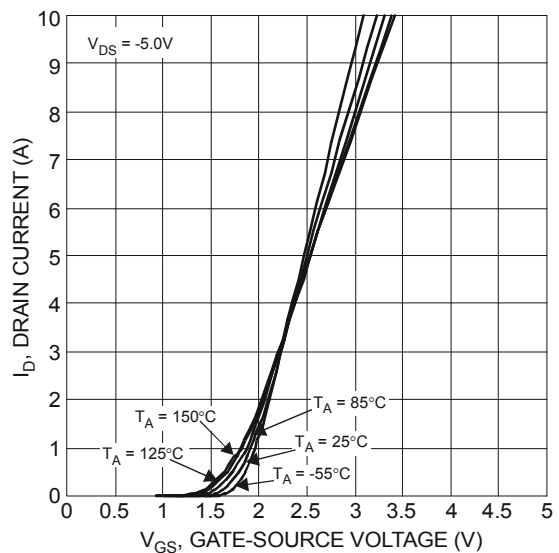


Figure 2 Typical Transfer Characteristics

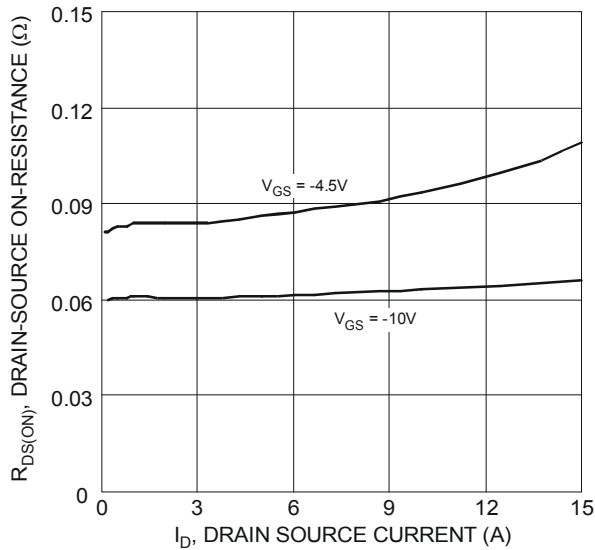


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

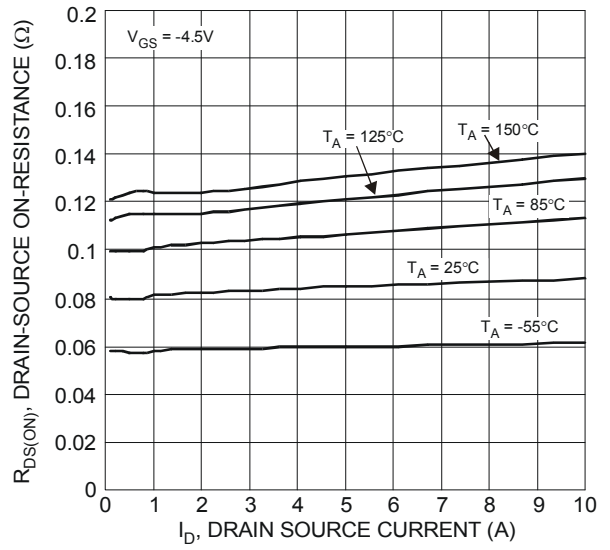


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

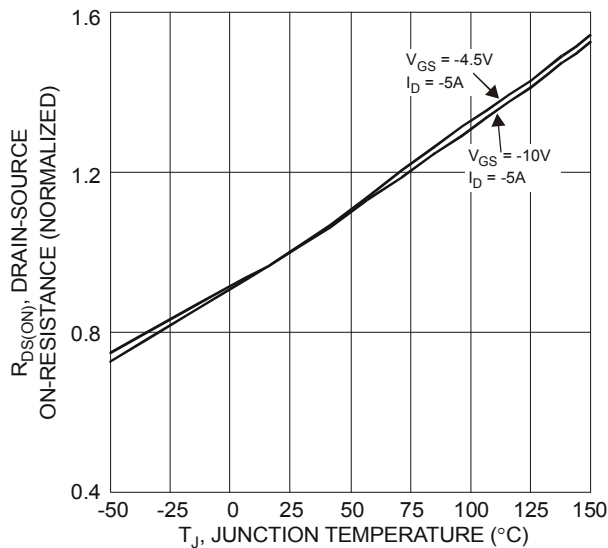


Figure 5 On-Resistance Variation with Temperature

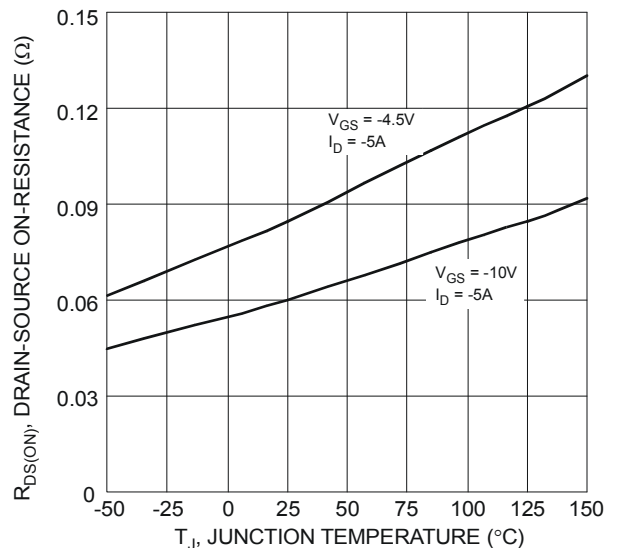


Figure 6 On-Resistance Variation with Temperature

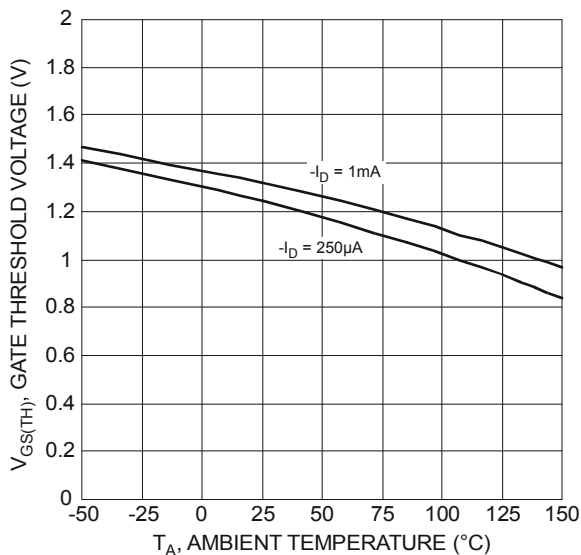


Figure 7 Gate Threshold Variation vs. Ambient Temperature

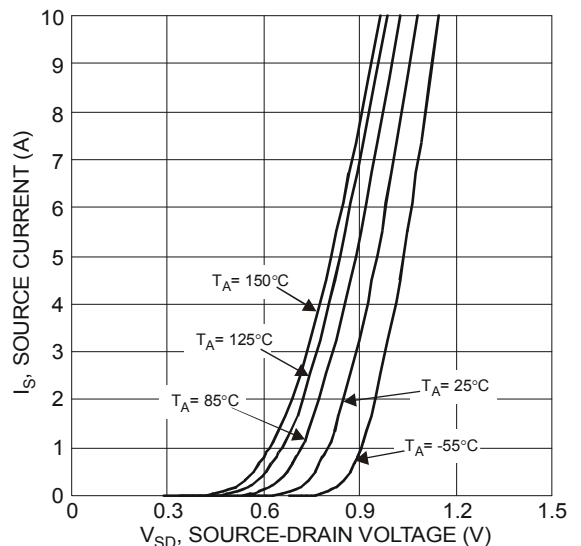
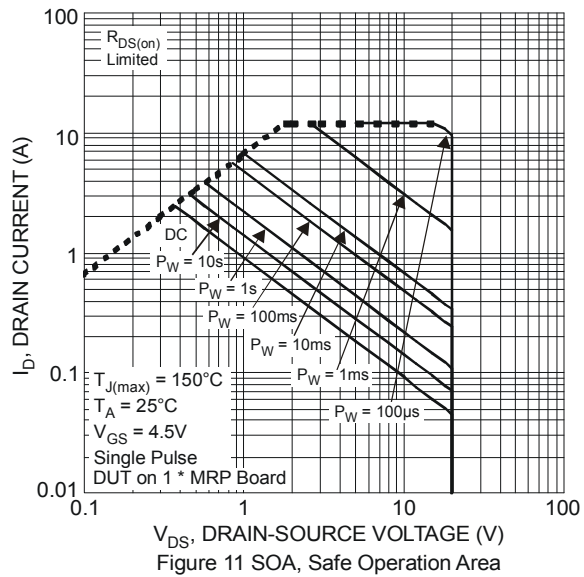
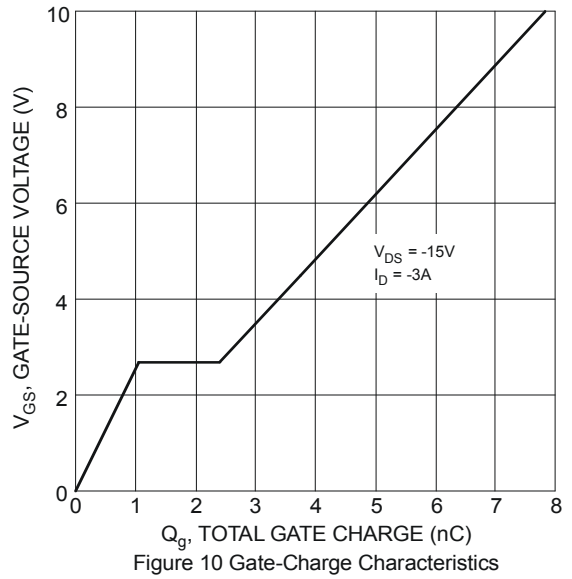
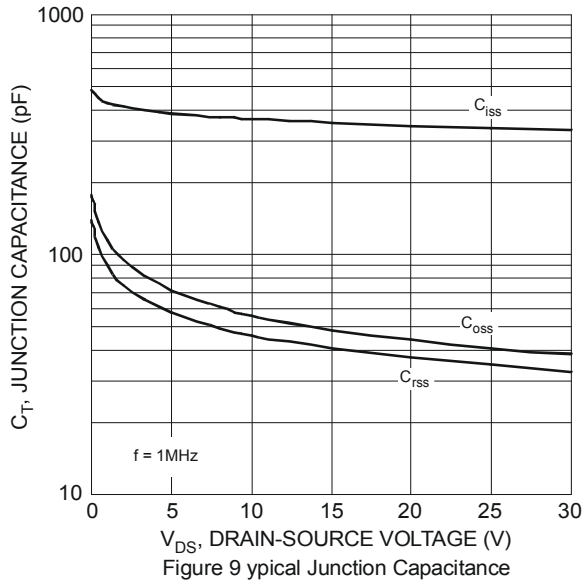


Figure 8 Diode Forward Voltage vs. Current



Electrical Characteristics – SCHOTTKY – D1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 8)	V _{(BR)R}	20	35	—	V	I _R = 1mA
Forward Voltage (Note 8)	V _F	—	—	0.40 0.47	V	I _F = 0.5A I _F = 1.0A
Reverse Current (Note 8)	I _R	—	30	80	μA	V _R = 20V

Notes: 8. Short duration pulse test used to minimize self-heating effect.

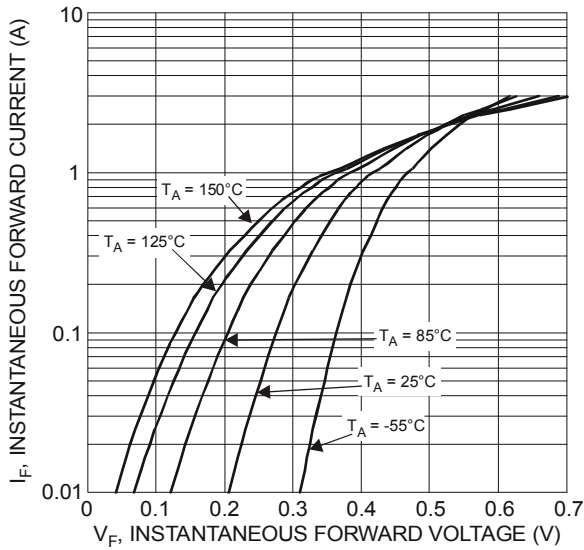


Figure 12 Typical Forward Characteristics

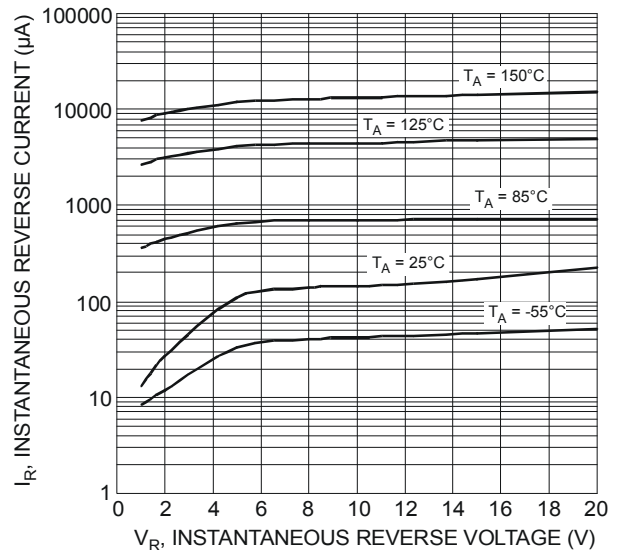
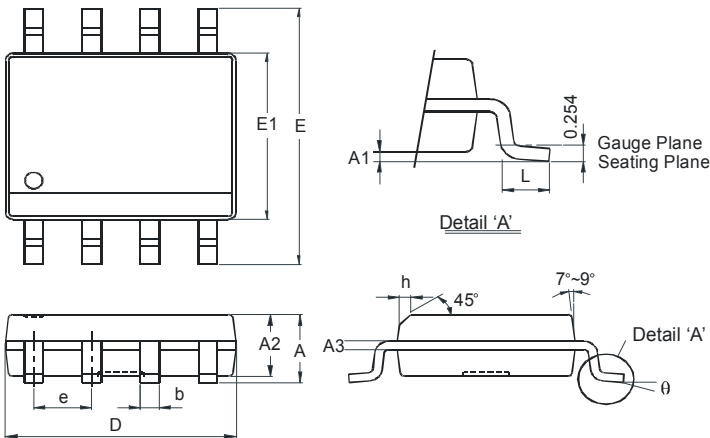


Figure 13 Typical Reverse Characteristics

Package Outline Dimensions

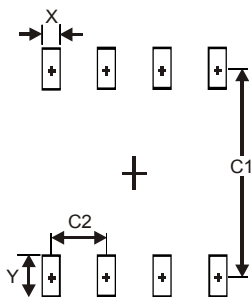
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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